

<IGBT Modules>

CM400C1Y-24S

HIGH POWER SWITCHING USE
INSULATED TYPE


dual (AC switch)

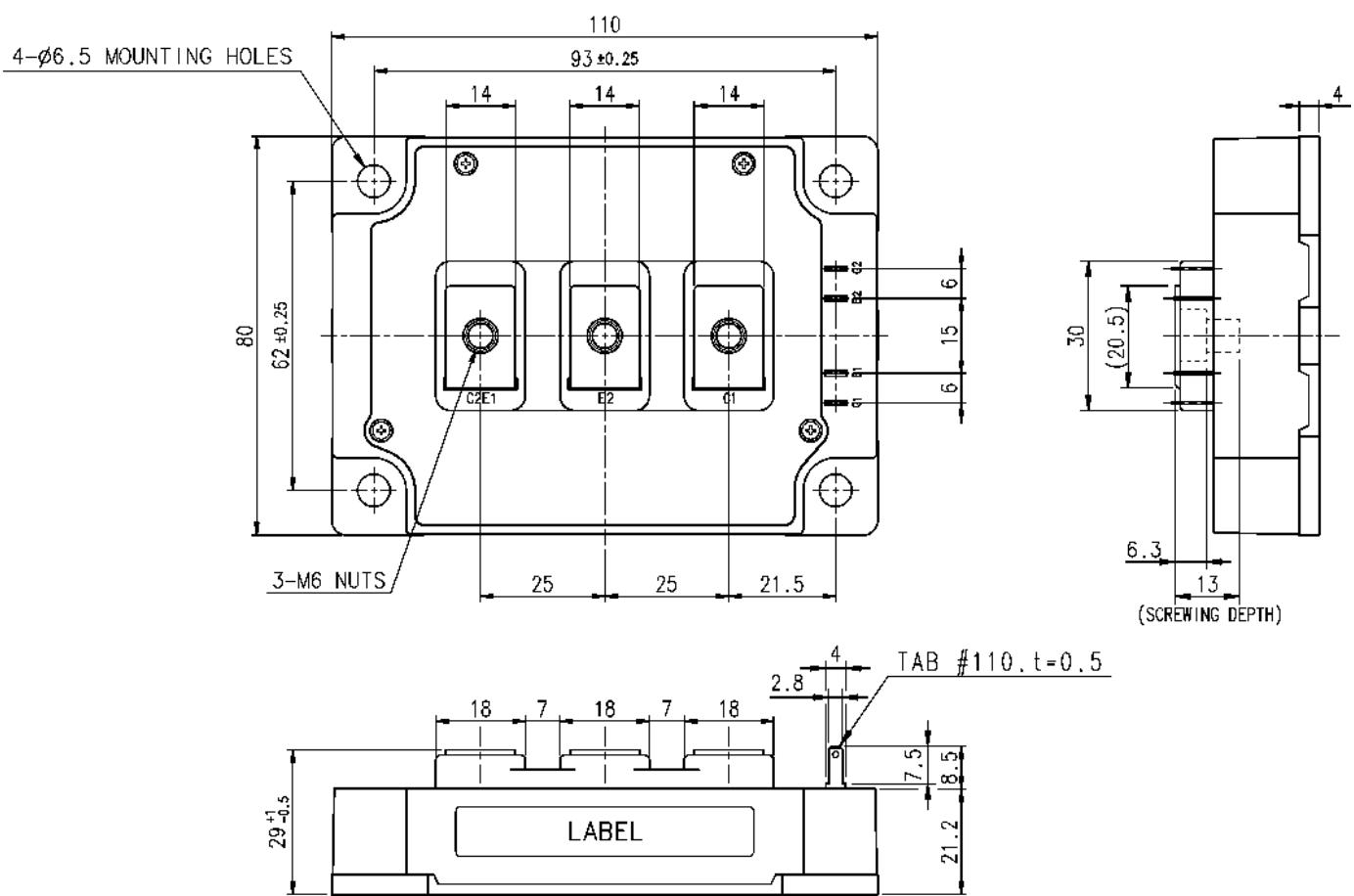
Collector current I_C	3 5 0 A*
Collector-emitter voltage V_{CES}	1 2 0 0 V
Maximum junction temperature $T_{j\max}$	1 7 5 °C
<ul style="list-style-type: none"> • Flat base Type • Copper base plate • RoHS Directive compliant • UL Recognized under UL1557, File E323585 	
*. DC current rating is limited by power terminals.	

APPLICATION

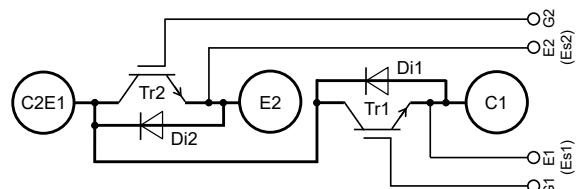
AC Power Switch for NPC

OUTLINE DRAWING & INTERNAL CONNECTION

Dimension in mm

**INTERNAL CONNECTION**

Tolerance otherwise specified	
Division of Dimension	Tolerance
0.5 to 3	±0.2
over 3 to 6	±0.3
over 6 to 30	±0.5
over 30 to 120	±0.8
over 120 to 400	±1.2



MAXIMUM RATINGS (T_j=25 °C, unless otherwise specified)

Symbol	Item	Conditions	Rating	Unit
V _{CES}	Collector-emitter voltage	G-E short-circuited	1200	V
V _{GES}	Gate-emitter voltage	C-E short-circuited	±20	V
I _C	Collector current	DC, T _C =124 °C (Note2, 4)	350 *	A
I _{CRM}		Pulse, Repetitive (Note3)	800	
P _{tot}	Total power dissipation	T _C =25 °C (Note2, 4)	2670	W
I _E (Note1)	Emitter current	(Note2)	350 *	A
I _{ERM} (Note1)		Pulse, Repetitive (Note3)	800	
V _{isol}	Isolation voltage	Terminals to base plate, RMS, f=60 Hz, AC 1 min	2500	V
T _{jmax}	Maximum junction temperature	Instantaneous event (overload)	175	°C
T _{cmax}	Maximum case temperature	(Note4)	125	
T _{jop}	Operating junction temperature	Continuous operation (under switching)	-40 ~ +150	°C
T _{stg}	Storage temperature	-	-40 ~ +125	

ELECTRICAL CHARACTERISTICS (T_j=25 °C, unless otherwise specified)

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
I _{CES}	Collector-emitter cut-off current	V _{CE} =V _{CES} , G-E short-circuited	-	-	1.0	mA
I _{GES}	Gate-emitter leakage current	V _{GE} =V _{GES} , C-E short-circuited	-	-	0.5	µA
V _{GE(th)}	Gate-emitter threshold voltage	I _C =40 mA, V _{CE} =10 V	5.4	6.0	6.6	V
V _{CEsat} (Terminal)	Collector-emitter saturation voltage	I _C =400 A (Note5), V _{GE} =15 V, Terminal, Refer to figure of test circuit	T _j =25 °C	-	1.85	2.30
			T _j =125 °C	-	2.05	-
			T _j =150 °C	-	2.10	-
V _{CEsat} (Chip)	Collector-emitter saturation voltage	I _C =400 A (Note5), V _{GE} =15 V, Chip	T _j =25 °C	-	1.70	2.15
			T _j =125 °C	-	1.90	-
			T _j =150 °C	-	1.95	-
C _{ies}	Input capacitance	V _{CE} =10 V, G-E short-circuited	-	-	40	nF
C _{oes}	Output capacitance		-	-	8.0	
C _{res}	Reverse transfer capacitance		-	-	0.66	
Q _G	Gate charge	V _{CC} =600 V, I _C =400 A, V _{GE} =15 V	-	934	-	nC
t _{d(on)}	Turn-on delay time	V _{CC} =600 V, I _C =400 A, V _{GE} =±15 V, R _G =0 Ω, Inductive load	-	-	800	ns
t _r	Rise time		-	-	200	
t _{d(off)}	Turn-off delay time		-	-	600	
t _f	Fall time		-	-	300	
V _{EC} (Note1) (Terminal)	Emitter-collector voltage	I _E =400 A (Note5), G-E short-circuited, Terminal, Refer to figure of test circuit	T _j =25 °C	-	1.85	2.30
			T _j =125 °C	-	1.85	-
			T _j =150 °C	-	1.85	-
V _{EC} (Note1) (Chip)	Emitter-collector voltage	I _E =400 A (Note5), G-E short-circuited, Chip	T _j =25 °C	-	1.70	2.15
			T _j =125 °C	-	1.70	-
			T _j =150 °C	-	1.70	-
t _{rr} (Note1)	Reverse recovery time	V _{CC} =600 V, I _E =400 A, V _{GE} =±15 V, R _G =0 Ω, Inductive load	-	-	300	ns
Q _{rr} (Note1)	Reverse recovery charge		-	21.4	-	µC
E _{on}	Turn-on switching energy per pulse	V _{CC} =600 V, I _C =I _E =400 A, V _{GE} =±15 V, R _G =0 Ω, T _j =150 °C, Inductive load	-	39.8	-	mJ
E _{off}	Turn-off switching energy per pulse		-	44.9	-	
E _{rr} (Note1)	Reverse recovery energy per pulse		-	35.2	-	
r _g	Internal gate resistance	Per switch	-	4.9	-	Ω

THERMAL RESISTANCE CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
$R_{th(j-c)Q}$	Thermal resistance ^(Note4)	Junction to case, per IGBT	-	-	56	K/kW
$R_{th(j-c)D}$		Junction to case, per DIODE	-	-	95	K/kW
$R_{th(c-s)}$	Contact thermal resistance ^(Note4)	Case to heat sink, per 1/2 module, Thermal grease applied ^(Note6)	-	18	-	K/kW

MECHANICAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
M_t	Mounting torque	Main terminals	M 6 screw	3.5	4.0	4.5
M_s		Mounting to heat sink	M 6 screw	3.5	4.0	4.5
m	Weight	-	-	580	-	g
e_c	Flatness of base plate	On the centerline X, Y ^(Note7)	-100	-	+100	μm

This product is compliant with the Restriction of the Use of Certain Hazardous Substances in Electrical and Electronic Equipment (RoHS) directive 2011/65/EU.

Note1. Represent ratings and characteristics of the anti-parallel, emitter-collector free-wheeling diode (DIODE).

2. Junction temperature (T_j) should not increase beyond $T_{j\max}$ rating.

3. Pulse width and repetition rate should be such that the device junction temperature (T_j) dose not exceed $T_{j\max}$ rating.

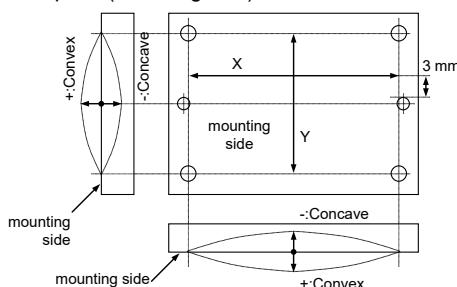
4. Case temperature (T_c) and heat sink temperature (T_s) are defined on the each surface (mounting side) of base plate and heat sink just under the chips. Refer to the figure of chip location.

The heat sink thermal resistance should measure just under the chips.

5. Pulse width and repetition rate should be such as to cause negligible temperature rise. Refer to the figure of test circuit.

6. Typical value is measured by using thermally conductive grease of $\lambda=0.9 \text{ W}/(\text{m}\cdot\text{K})$.

7. Base plate (mounting side) flatness measurement points (X, Y) are as follows of the following figure.



*. DC current rating is limited by power terminals.

RECOMMENDED OPERATING CONDITIONS

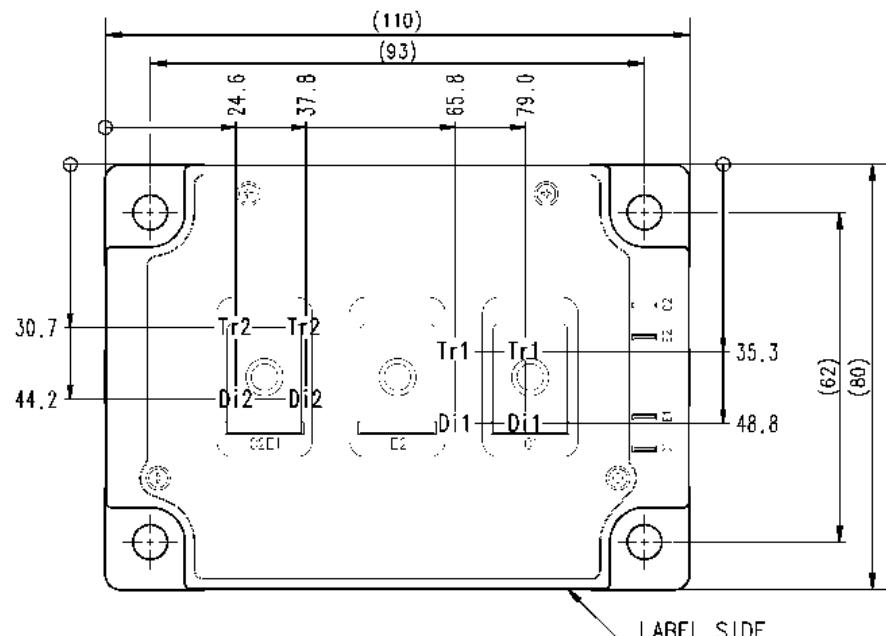
Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
V_{CC}	(DC) Supply voltage	Applied across C1-E2	-	600	850	V
V_{GEon}	Gate (-emitter drive) voltage	Applied across G1-Es1/G2-Es2	13.5	15.0	16.5	V
R_G	External gate resistance	Per switch	0	-	10	Ω

CM400C1Y-24S

HIGH POWER SWITCHING USE INSULATED TYPE

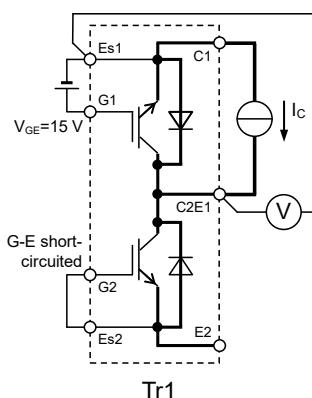
CHIP LOCATION (Top view)

Dimension in mm, tolerance: ± 1 mm

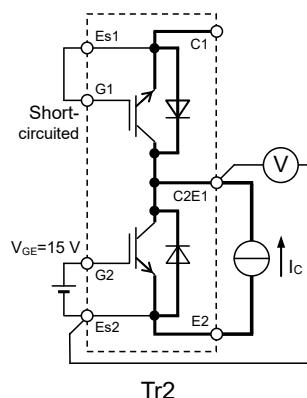


Tr1/Tr2: IGBT, Di1/Di2: DIODE

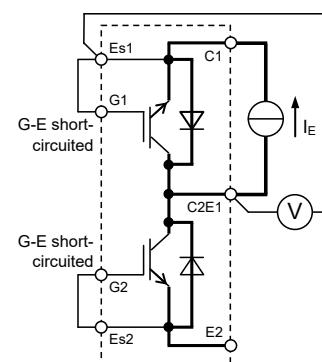
TEST CIRCUIT



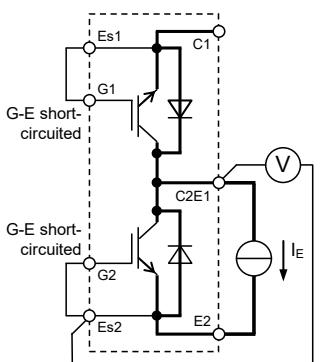
V_{CEsat} test circuit



Tr2

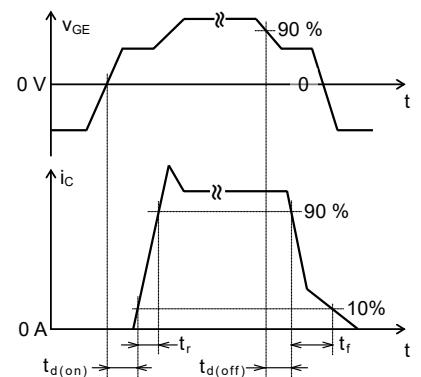
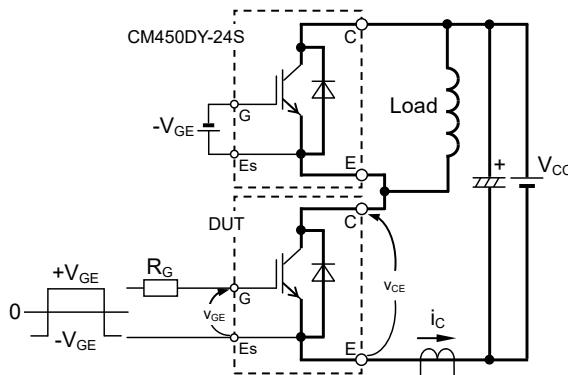


Di1

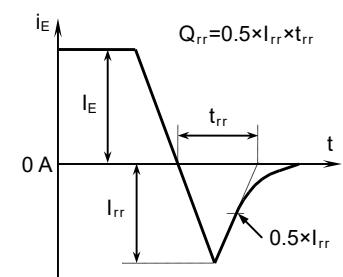
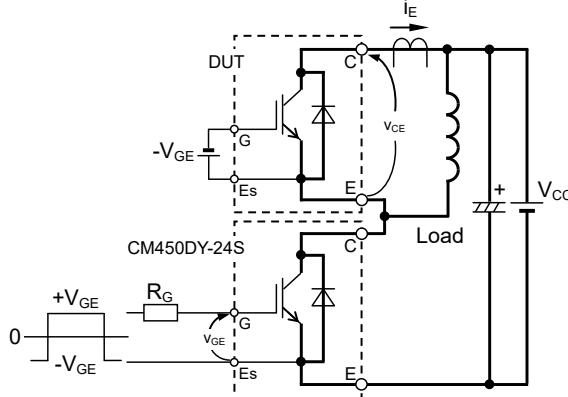


V_{EC} test circuit

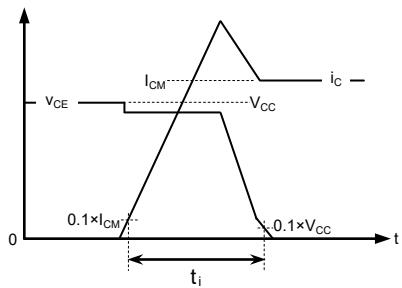
TEST CIRCUIT AND WAVEFORMS



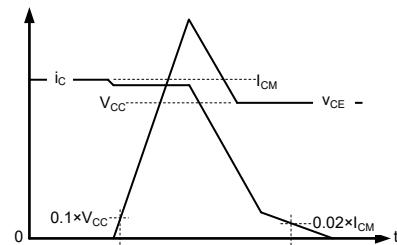
Switching characteristics test circuit and waveform



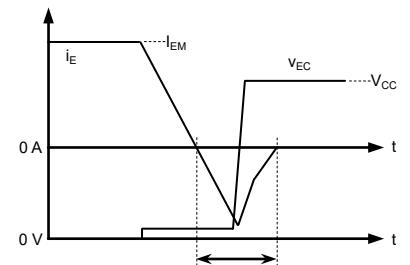
Reverse recovery characteristics (t_{rr} , Q_{rr}) test circuit



IGBT Turn-on switching energy



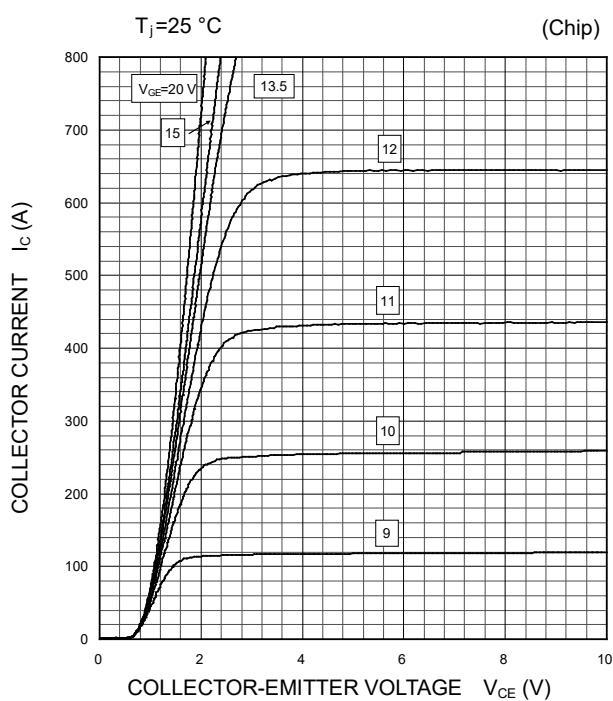
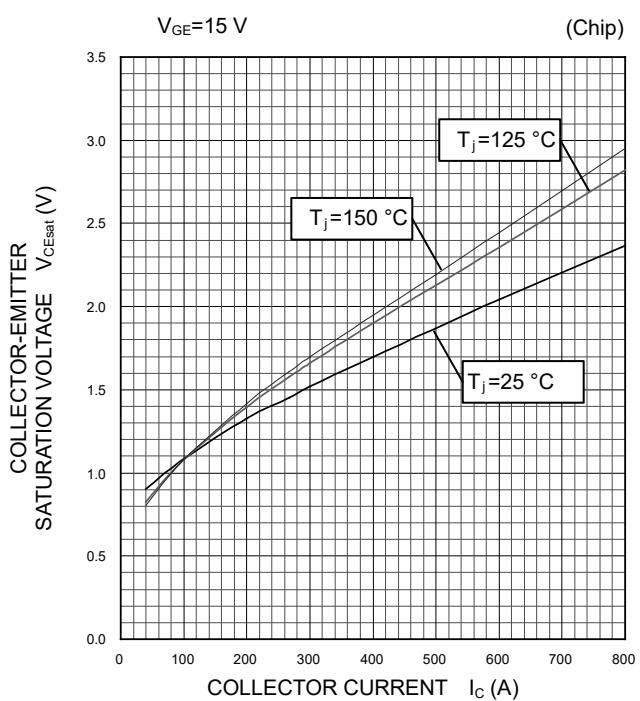
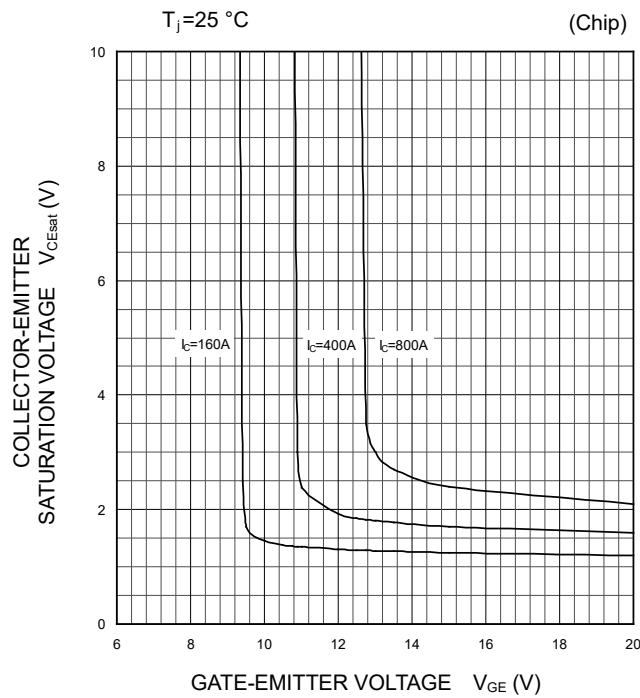
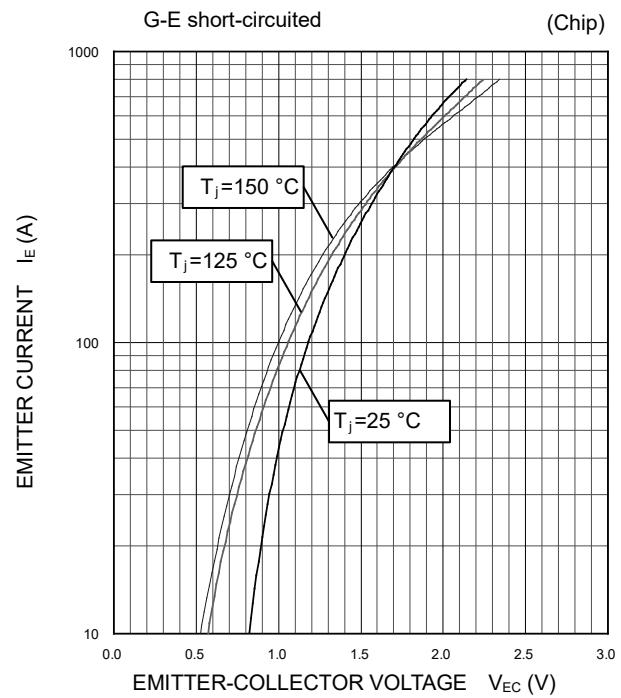
IGBT Turn-off switching energy



DIODE Reverse recovery energy

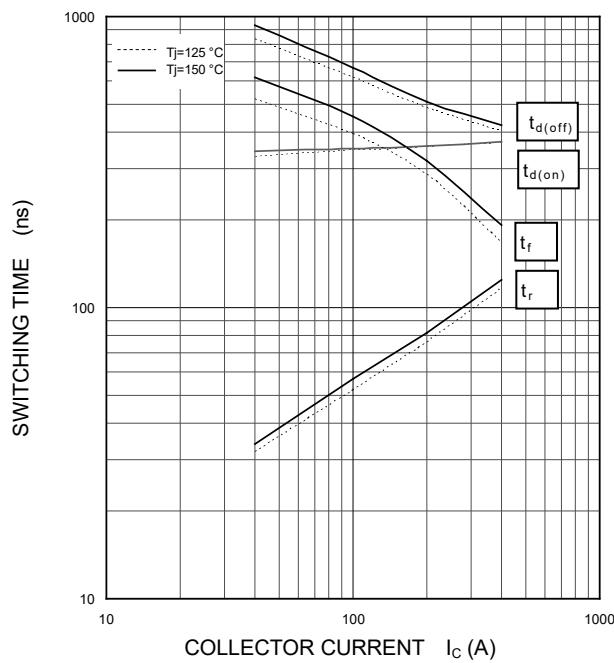
Turn-on / Turn-off switching energy and Reverse recovery energy test waveforms (Integral time instruction drawing)

PERFORMANCE CURVES

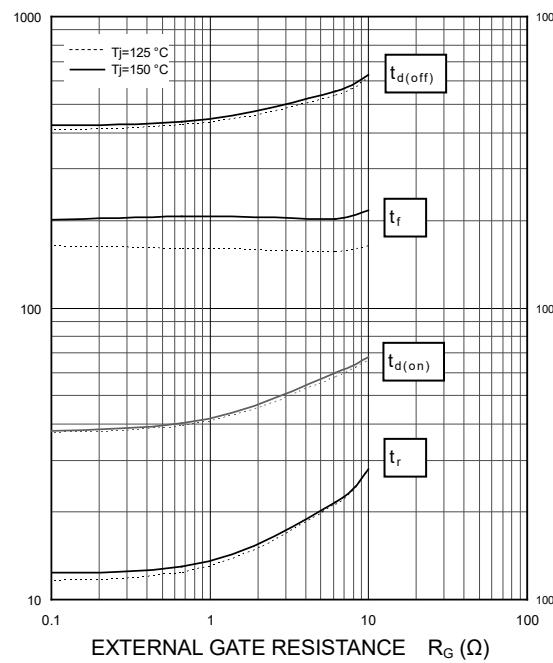
OUTPUT CHARACTERISTICS
(TYPICAL)COLLECTOR-EMITTER SATURATION
VOLTAGE CHARACTERISTICS
(TYPICAL)COLLECTOR-EMITTER SATURATION
VOLTAGE CHARACTERISTICS
(TYPICAL)FREE WHEELING DIODE
FORWARD CHARACTERISTICS
(TYPICAL)

PERFORMANCE CURVES

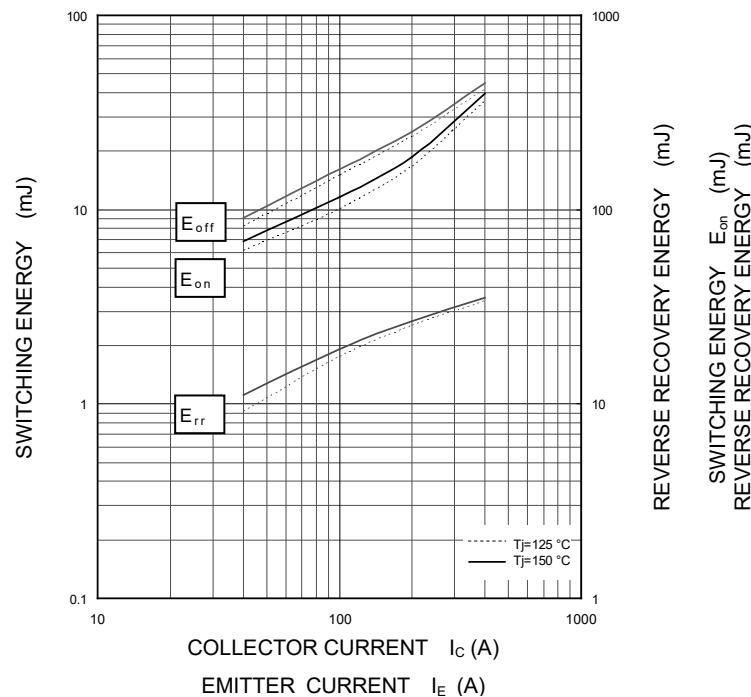
HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)
 $V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $R_G=0\text{ }\Omega$,
INDUCTIVE LOAD



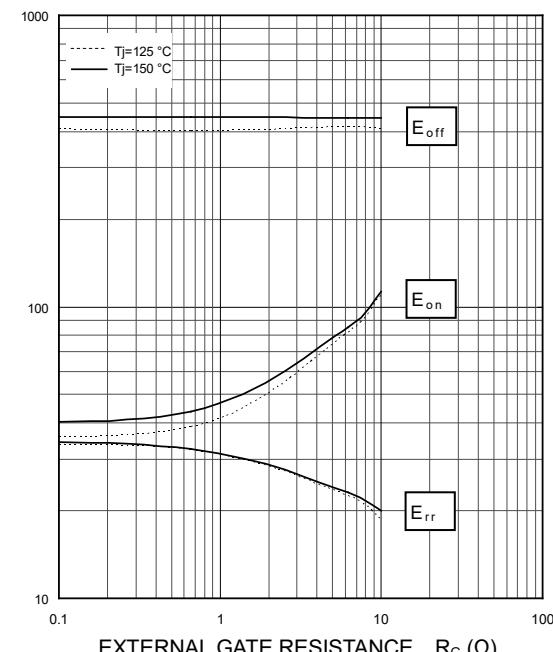
HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)
 $V_{CC}=600\text{ V}$, $I_c=400\text{ A}$, $V_{GE}=\pm 15\text{ V}$,
INDUCTIVE LOAD



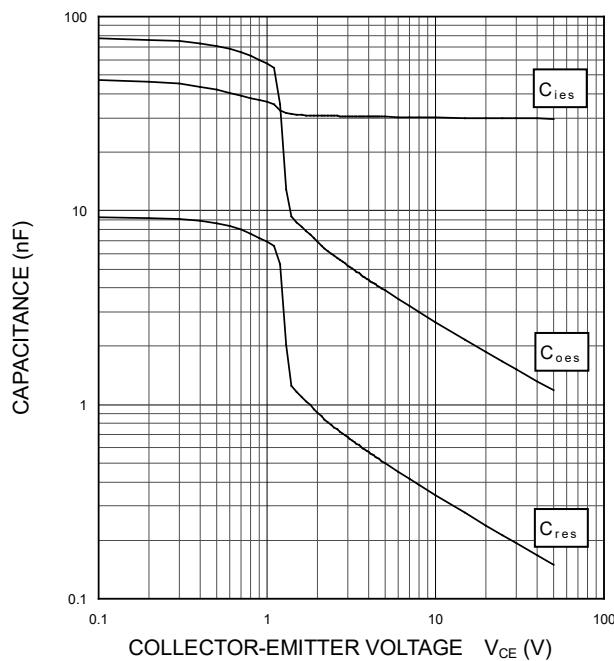
HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)
 $V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $R_G=0\text{ }\Omega$,
INDUCTIVE LOAD, PER PULSE



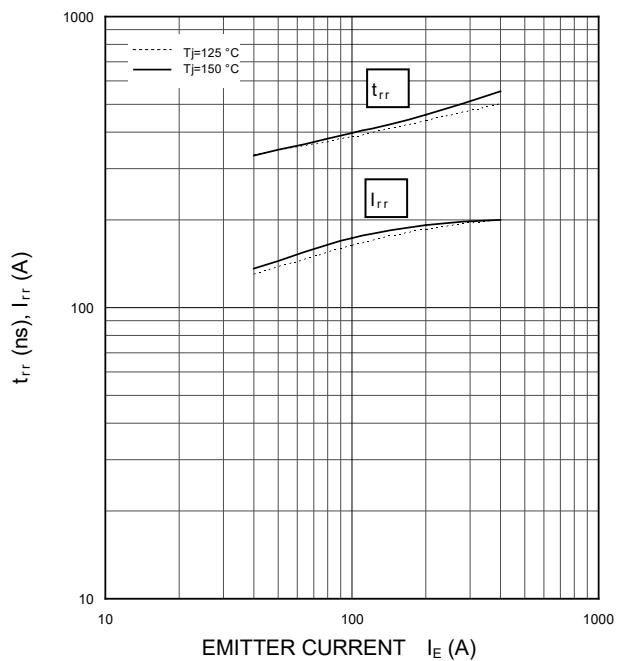
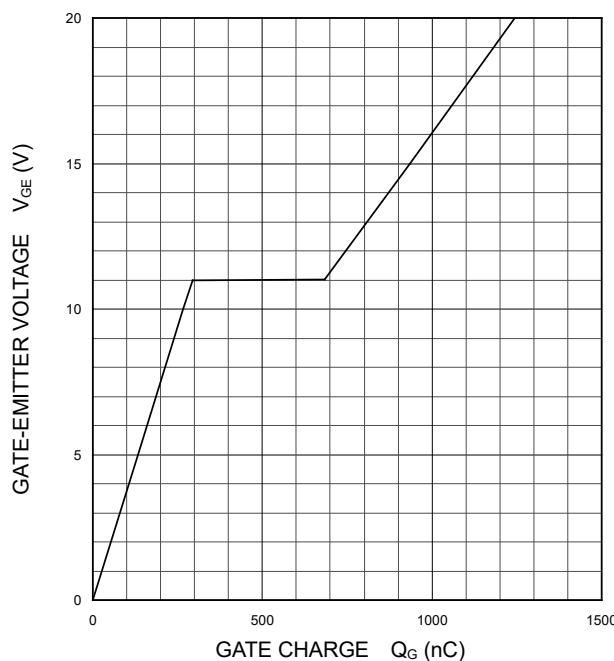
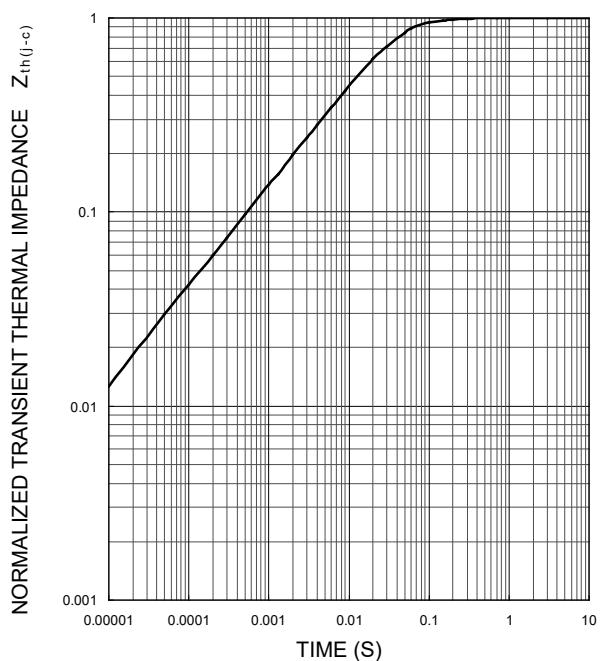
HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)
 $V_{CC}=600\text{ V}$, $I_c/I_e=400\text{ A}$, $V_{GE}=\pm 15\text{ V}$,
INDUCTIVE LOAD, PER PULSE



PERFORMANCE CURVES

CAPACITANCE CHARACTERISTICS
(TYPICAL)G-E short-circuited, $T_j=25^\circ\text{C}$ FREE WHEELING DIODE
REVERSE RECOVERY CHARACTERISTICS
(TYPICAL) $V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $R_G=0\ \Omega$,

INDUCTIVE LOAD

GATE CHARGE CHARACTERISTICS
(TYPICAL) $V_{CC}=600\text{ V}$, $I_C=400\text{ A}$, $T_j=25^\circ\text{C}$ TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS
(MAXIMUM)Single pulse, $T_C=25^\circ\text{C}$ $R_{th(j-c)Q}=56\text{ K/kW}$, $R_{th(j-c)D}=95\text{ K/kW}$ 

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